

N-channel MOS-FET			
450V	0,45Ω	18A	125W

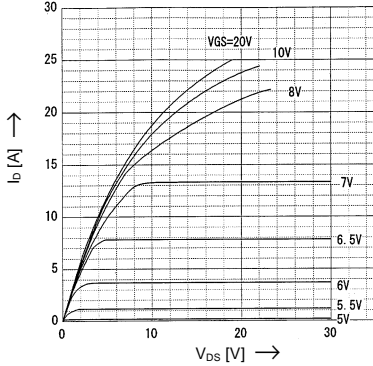
2SK2755-01

FAP-IIS Series

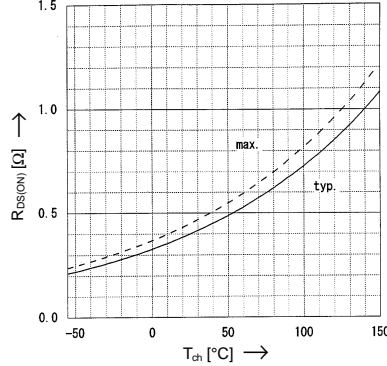


> Characteristics

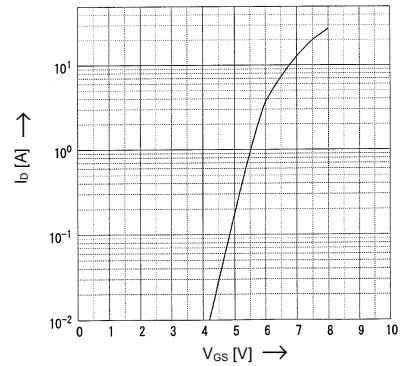
Typical Output Characteristics
 $I_D = f(V_{DS})$; 80μs pulse test; $T_{ch} = 25^\circ\text{C}$



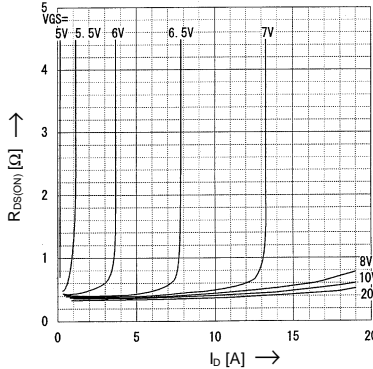
Drain-Source On-State Resistance vs. T_{ch}
 $R_{DS(on)} = f(T_{ch})$; $I_D = 9\text{A}$; $V_{GS} = 10\text{V}$



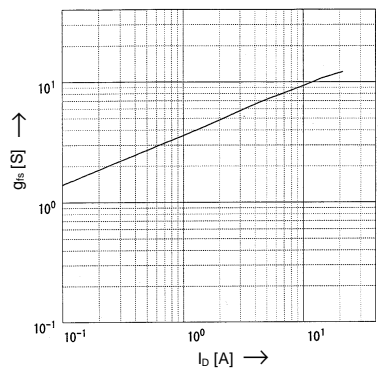
Typical Transfer Characteristics
 $I_D = f(V_{GS})$; 80μs pulse test; $V_{DS} = 25\text{V}$; $T_{ch} = 25^\circ\text{C}$



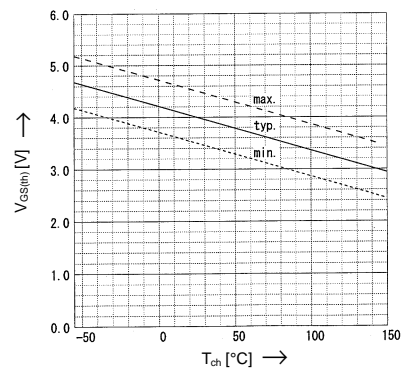
Typical Drain-Source On-State-Resistance vs. I_D
 $R_{DS(on)} = f(I_D)$; 80μs pulse test; $T_{ch} = 25^\circ\text{C}$



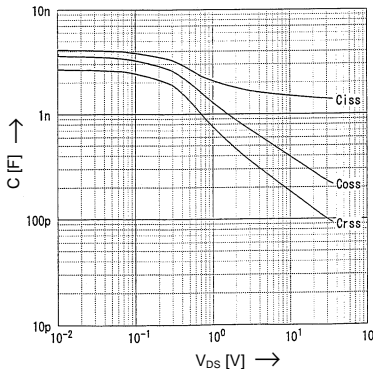
Typical Forward Transconductance vs. I_D
 $g_{fs} = f(I_D)$; 80μs pulse test; $V_{DS} = 25\text{V}$; $T_{ch} = 25^\circ\text{C}$



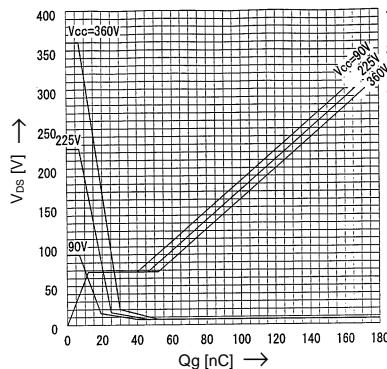
Gate Threshold Voltage vs. T_{ch}
 $V_{GS(th)} = f(T_{ch})$; $I_D = 1\text{mA}$; $V_{DS} = V_{GS}$



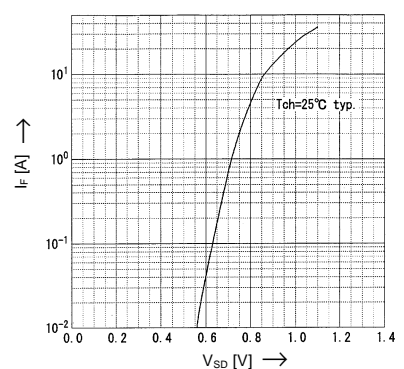
Typical Capacitances vs. V_{DS}
 $C = f(V_{DS})$; $V_{GS} = 0\text{V}$; $f = 1\text{MHz}$



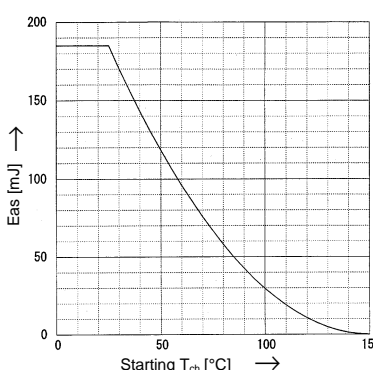
Typical Gate Charge Characteristic
 $V_{GS} = f(Q_g)$; $I_D = 18\text{A}$; $T_{ch} = 25^\circ\text{C}$



Forward Characteristics of Reverse Diode
 $I_F = f(V_{SD})$; 80μs pulse test; $V_{GS} = 0\text{V}$



Avalanche Energy Derating
 $E_{as} = f(\text{starting } T_{ch})$; $V_{CC} = 45\text{V}$; $I_{AV} = 18\text{A}$



Safe Operation Area
 $I_D = f(V_{DS})$; $D = 0.01$; $T_{ch} = 25^\circ\text{C}$

